

CMP200N25/CMB200N25/CMI200N25/CMF200N25

250V, 17mΩ typ., 90A N-Channel MOSFET

General Description

The 200N25 uses advanced SGT technology to provide excellent RDS(ON). This device is suitable for use as a Battery protection or in other Switching application.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

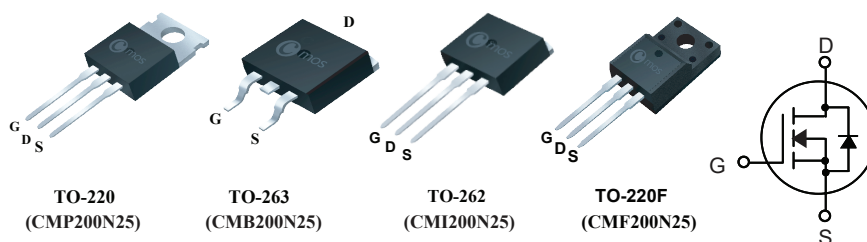
Product Summary

BVDSS	R _{DS(on)} max.	ID
250V	19mΩ	90A

Applications

- DC/DC Converter
- Battery management System
- Uninterruptible Power Supply

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	250		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current	90	90*	A
I _D @T _C =100°C	Continuous Drain Current	57	57*	A
I _{DM}	Pulsed Drain Current	360	360*	A
EAS	Single Pulse Avalanche Energy (Note 1)	2030		mJ
P _D @T _C =25°C	Total Power Dissipation	300	50	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62	62	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.42	2.50	°C/W

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	250	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	17	19	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=250V$, $V_{GS}=0V$	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=18A$	---	51	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3.7	---	Ω
Q_g	Total Gate Charge	$V_{DS}=125V$, $I_D=40A$ $V_{GS}=10V$	---	72	---	nC
Q_{gs}	Gate-Source Charge		---	28.6	---	
Q_{gd}	Gate-Drain Charge		---	12.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=125V$, $V_{GS}=10V$ $R_{G_ext}=2.7\Omega$	---	15	---	ns
T_r	Rise Time		---	55	---	
$T_{d(off)}$	Turn-Off Delay Time		---	56	---	
T_f	Fall Time		---	51.5	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4600	---	pF
C_{oss}	Output Capacitance		---	3000	---	
C_{rss}	Reverse Transfer Capacitance		---	180	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	90	A
I_{SM}	Pulsed Source Current		---	---	360	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	0.81	1.2	V
t_{rr}	Reverse Recovery Time	$di/dt = 100A/\mu s$	---	156	---	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 40A$	---	1118	---	nC

Note :

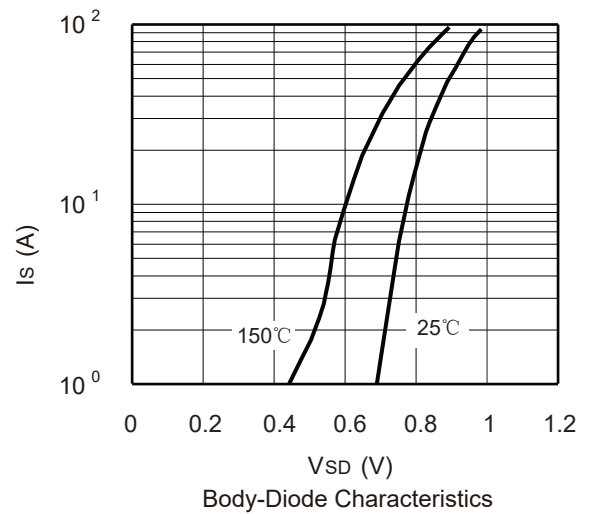
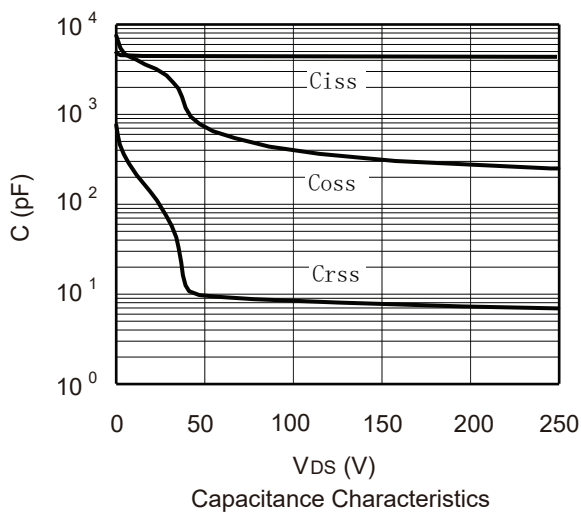
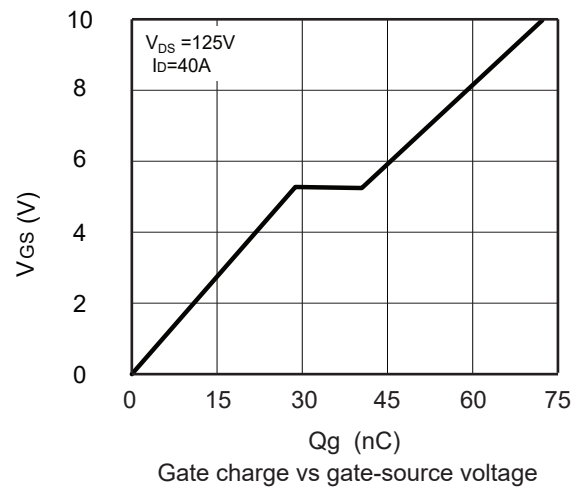
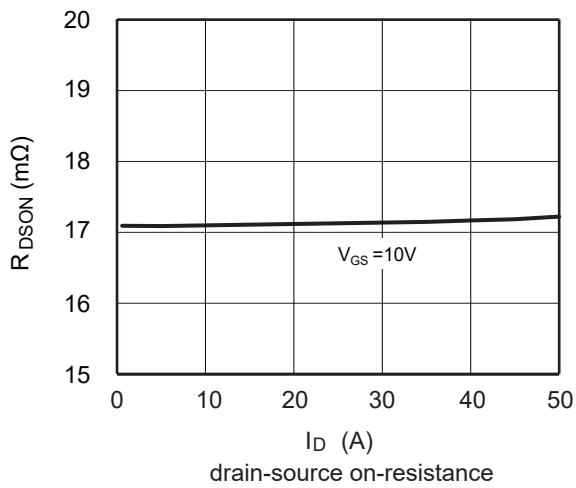
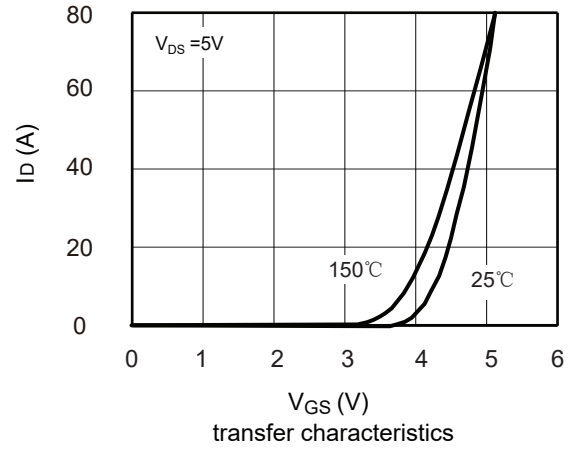
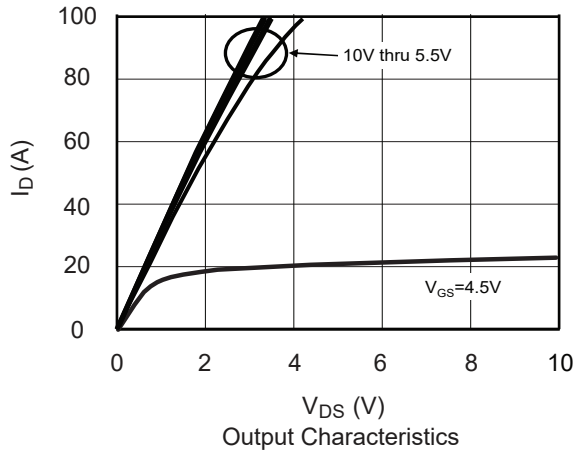
1.The EAS data shows Max. rating .The test condition is $V_{DS}=80V$, $V_{GS}=10V$, $L=5mH$, $I_{AS}=28.5A$.

This product has been designed and qualified for the consumer market.

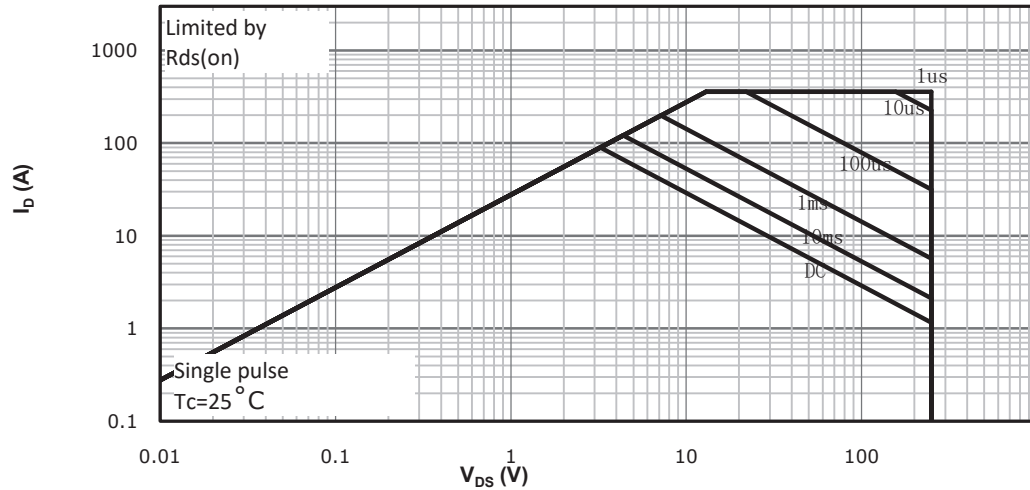
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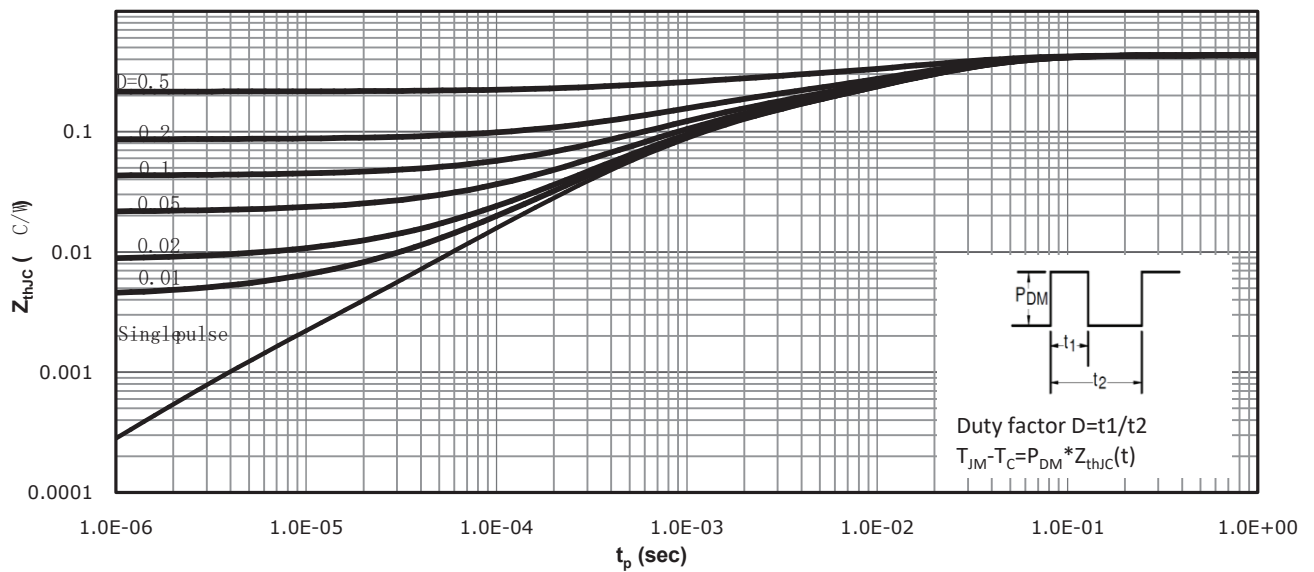
Typical Characteristics



Typical Characteristics



Safe Operating Area



Max. Transient Thermal Impedance

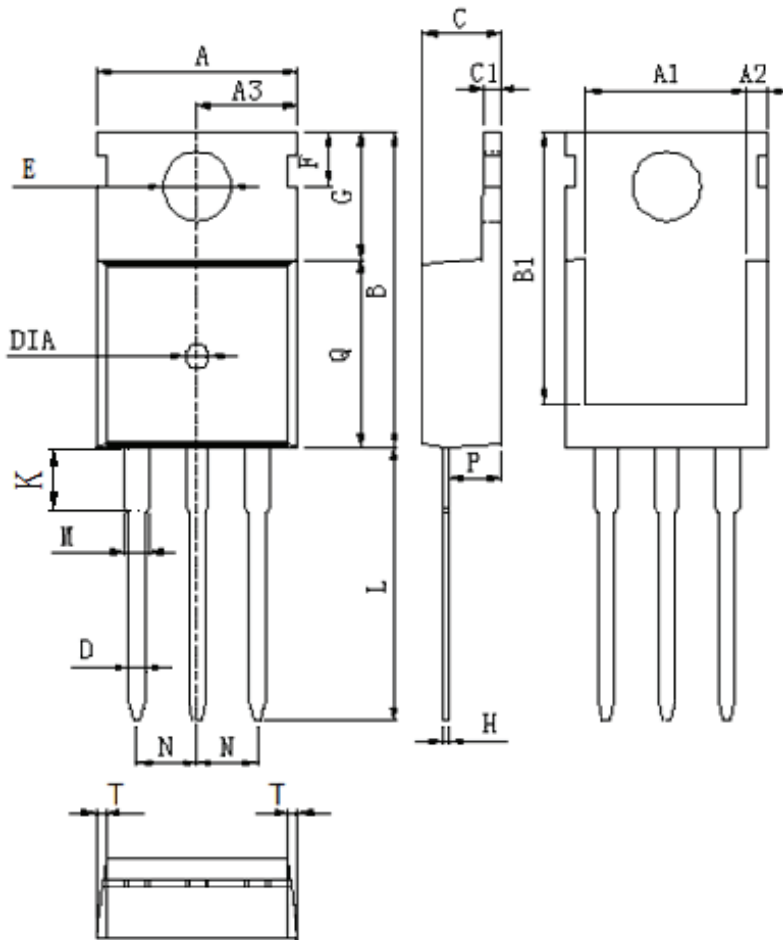
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Package Dimension

TO-220

Unit :mm



DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5(deep 0.2)

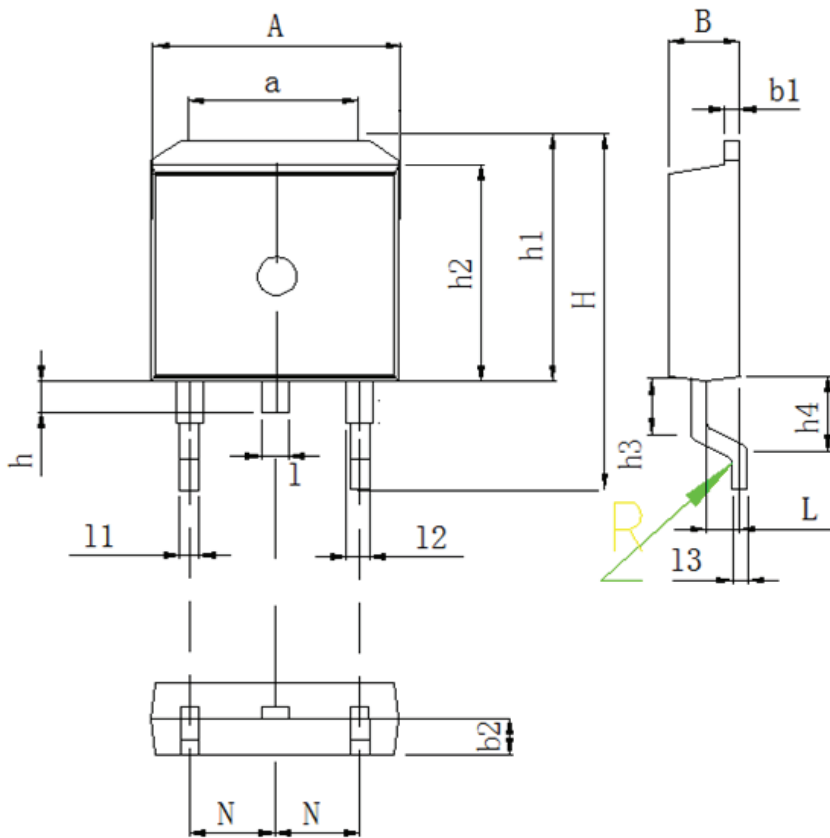
CMP200N25/CMB200N25/CMI200N25/CMF200N25

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Package Dimension

TO-263

Unit :mm

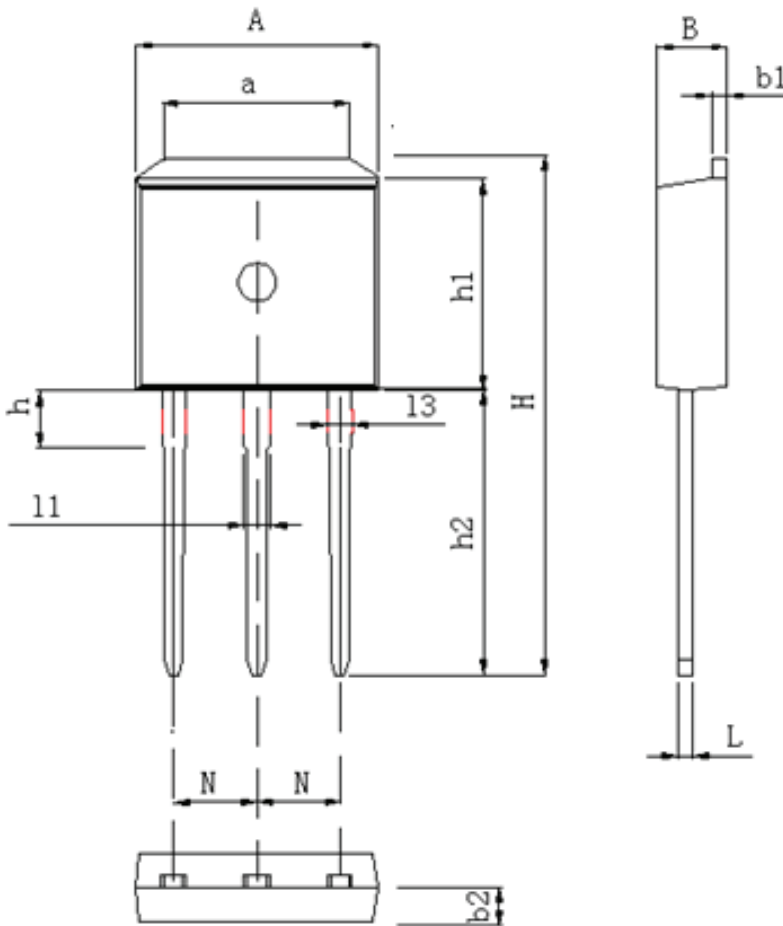


DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

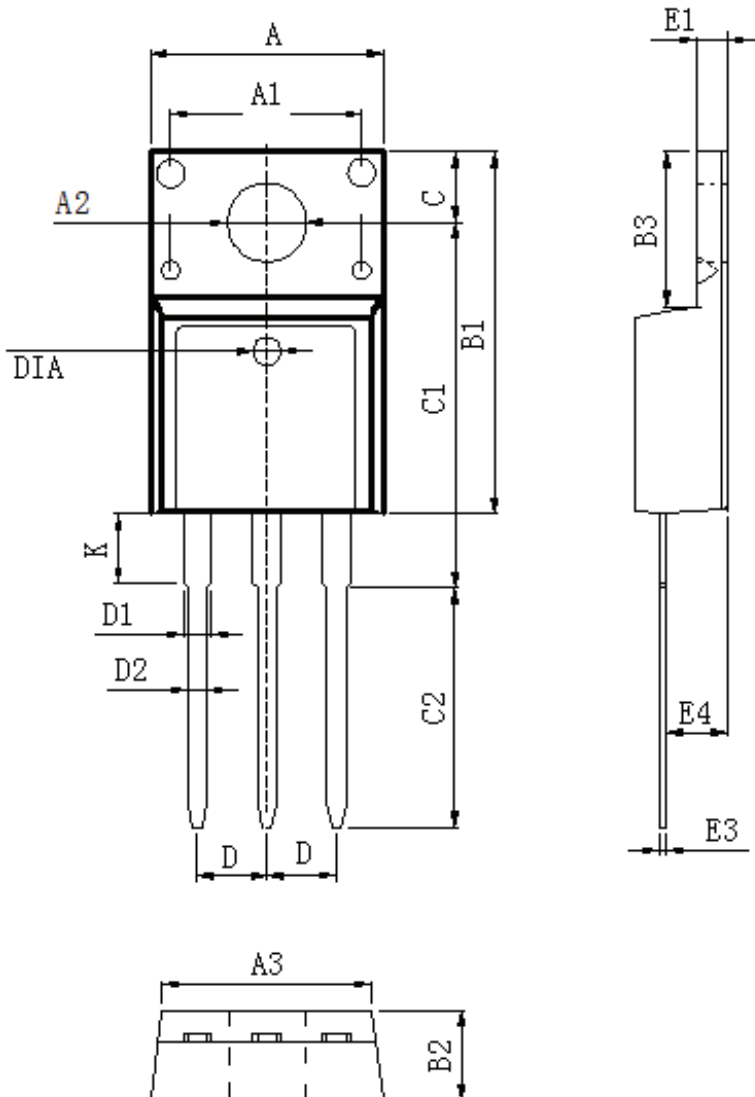
Package Dimension

TO-262

Unit :mm



DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
l1	1.3 ± 0.1
l2	0.8 ± 0.1
N	2.45 ± 0.1

Package Dimension
TO-220F
Unit :mm


DIM	MILLIMETERS
A	10.16 ± 0.3
A1	7.00 ± 0.1
A2	3.3 ± 0.2
A3	9.5 ± 0.2
B1	15.87 ± 0.3
B2	4.7 ± 0.2
B3	6.68 ± 0.4
C	3.3 ± 0.2
C1	12.57 ± 0.3
C2	10.02 ± 0.5
D	2.54 ± 0.05
D1	1.28 ± 0.2
D2	0.8 ± 0.1
K	3.1 ± 0.3
E1	2.54 ± 0.1
E3	0.5 ± 0.1
E4	2.76 ± 0.2
DIA	$\odot 1.5$ (deep 0.2)